



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

## SOT-323 Plastic-Encapsulate DIODE

### MMBD4448W SWITCHING DIODE

#### FEATURES

Power dissipation

$P_D$ : 200 mW ( $T_{amb}=25^{\circ}C$ )

Collector current

$I_O$ : 250 mA

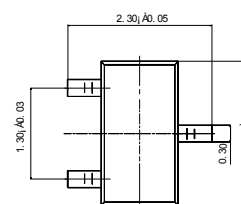
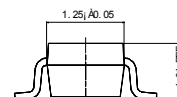
Collector-base voltage

$V_R$ : 75 V

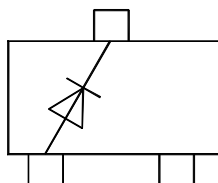
Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$

#### SOT-323



Unit: mm



Marking: KA3

#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

| Parameter                       | Symbol      | Test conditions                                          | MIN | MAX                        | UNIT    |
|---------------------------------|-------------|----------------------------------------------------------|-----|----------------------------|---------|
| Reverse breakdown voltage       | $V_{(BR)R}$ | $I_R=10\mu A$                                            | 75  |                            | V       |
| Reverse voltage leakage current | $I_R$       | $V_R=20V$<br>$V_R=75V$                                   |     | 0.025<br>2.5               | $\mu A$ |
| Forward voltage                 | $V_F$       | $I_F=5mA$<br>$I_F=10mA$<br>$I_F=100mA$<br>$I_F=150mA$    |     | 0.72<br>0.855<br>1<br>1.25 | V       |
| Diode capacitance               | $C_D$       | $V_R=0V, f=1MHz$                                         |     | 4                          | pF      |
| Reverse recovery time           | $t_{rr}$    | $I_F=I_R=10mA$<br>$I_{rr}=0.1 \times I_R, R_L=100\Omega$ |     | 4                          | nS      |

Test period  $<3000\mu s$ .